

isc Silicon PNP Power Transistor

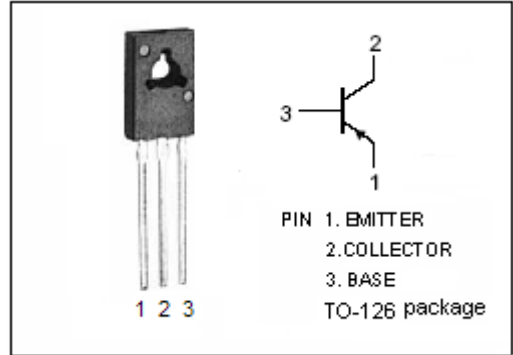
2SA1352

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -200V$  (Min)
- Complement to Type 2SC3416

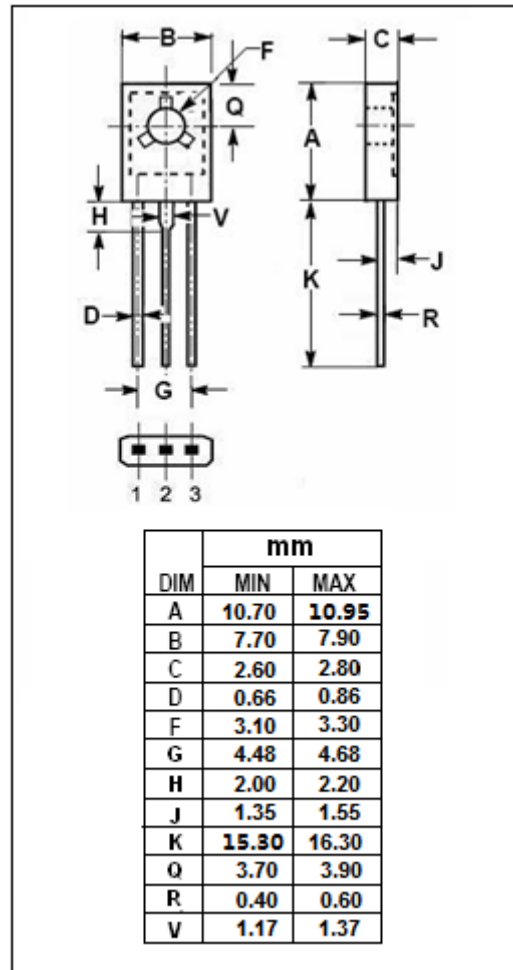
APPLICATIONS

- Designed for color TV chroma output, high-voltage driver applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-200	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V
I <sub>C</sub>	Collector Current-Continuous	-0.1	A
I <sub>CM</sub>	Collector Current-Peak	-0.2	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.2	W
	Total Power Dissipation @ T <sub>C</sub> =25°C	5	
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon PNP Power Transistor****2SA1352****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{ A}; I_E = 0$	-200			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{ A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -20\text{mA}; I_B = -2\text{mA}$			-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -20\text{mA}; I_B = -2\text{mA}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -150\text{V}; I_E = 0$			-0.1	$\mu\text{ A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	$\mu\text{ A}$
$h_{FE}$	DC Current Gain	$I_C = -10\text{mA}; V_{CE} = -40\text{V}$	40		320	
$f_T$	Current-Gain—Bandwidth Product	$I_C = -10\text{mA}; V_{CE} = -30\text{V}$		70		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -30\text{V}; f = 1.0\text{MHz}$		1.7		pF

◆  **$h_{FE}$  Classifications**

C	D	E	F
40-80	60-120	100-200	160-320